

Preparation of Silicon Nitride-Titanium Nitride and Titanium-Titanium Nitride Composites from (CH₃)₃SiNHTiCl₃-Coated Si₃N₄ and Ti Particles

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[(Trimethylsilyl)amino]titanium trichloride, $(CH_3)_3$ -SiNHTiCl $_3$, was isolated as a red-orange crystalline solid in 58% yield from the reaction of TiCl $_4$ with [(CH $_3$) $_3$ Si] $_2$ NH in 1:1 molar ratio in dichloromethane at -78° C. Pyrolysis of (CH $_3$) $_3$ SiNHTiCl $_3$ at 600°C furnished titanium nitride. This precursor is suitable for the preparation of composites and was employed to prepare Si $_3$ N $_4$ -TiN and Ti-TiN powders by adding Si $_3$ N $_4$ particles or titanium powders to a solution of (CH $_3$) $_3$ SiNHTiCl $_3$ in dichloromethane, drying and pyrolyzing the resulting solid. This precursor also has been used as a binder to prepare Si $_3$ N $_4$ -TiN and Ti-TiN bodies. Highresolution transmission electron microscopic studies of the Si $_3$ N $_4$ -TiN composite showed that titanium nitride is concentrated on the surface of the Si $_3$ N $_4$ particles.

I. Introduction

PRECERAMIC precursor processing has received extensive attention in recent years for the preparation of diverse advanced materials. This route has been suggested to offer numerous advantages over conventional methods. Low-temperature syntheses, control of the purity, and ease of preparation of materials in the desired forms of fibers, coatings, and films can be achieved by preceramic precursor processing. The chemistry of preceramic polymer pyrolysis routes for materials such as silicon nitride, silicon carbide, and boron nitride has been reviewed recently.

Preceramic precursor routes for the preparation of group 4 metal nitrides, with emphasis on titanium nitride, involving the preparation of polymers from amido or alkoxy compounds of group 4 elements also have been reported. For example, Maya *et al.* described the ammonolysis of titanium or zirconium tetrakis(dialkylamides) to obtain insoluble polymers whose pyrolysis gave the respective nitrides.⁴ The soluble polymers obtained in the reactions of Ti[N(CH₃)₂]₄ with primary amines⁵ have been used by Seyferth and Mignani⁶ in the pyrolytic generation of TiN. A minor variation of this route which employs Ti[N(C₃H₇)₂]₄ instead of Ti[N(CH₃)₂]₄ was reported subsequently by Mackenzie *et al.*⁷ Jiang and Rhine⁸ synthesized polymers by reacting furfuryl alcohol with titanium alkoxides. These polymers required pyrolysis in an ammonia atmosphere

in the temperature range of 800–1200°C to form amorphous titanium nitride and calcining at 1200–1500°C for crystallization. A monomer, FTi[N(SiMe₃)]₃, also has been proposed to form titanium nitride on the basis of thermoanalytical studies.⁹

Our current interest is focused toward new routes to group 4 materials and composites at low temperatures. 10,11 We recently described the photolytic decomposition of Ti[N(CH₃)₂]₄ on irradiation with 1.064-µm light from a pulsed Nd-YAG laser. The decomposition products were pyrolyzed to TiN at 1100°C. We also prepared TiN-Al₂O₃, TiN-TiO₂, and Si₃N₄-TiN composites by this method requiring pyrolysis in the 800-1100°C range. 11 These materials are useful for automotive applications. For example, titanium nitride-silicon nitride composites have been suggested as structural materials because of their superior mechanical properties. 12 Titanium nitride electrodes have been shown to outperform metallic ones in "sodium heat engines" (SHE).13 It should be pointed out that these composites are traditionally prepared by mechanically mixing the components and sintering or hot pressing.¹⁴ Recently, TiO₂ has also been used to prepare TiN/Si₃N₄ composites because of its ability to convert to TiN in the presence of N₂/H₂ at silicon nitriding temperature.¹⁵ Clearly, there is need for improved methods for preparation of composites with better distribution of

In this report, we describe the preparation of crystalline titanium nitride by the pyrolysis of [(trimethylsilyl)amino]titanium trichloride, (CH₃)₃SiNHTiCl₃, in ammonia at 600–800°C. The applications of this route are demonstrated by the preparation of Si₃N₄—TiN and Ti—TiN composites with the titanium nitride component concentrated on the surface of the substrate particles. An application of preceramic polymers developed by Yajima *et al.*¹⁶ and, more recently, Seyferth and Czubarow¹⁷ employs them as binders in powder metallurgy and ceramic powder processing.¹⁸ We have also investigated the suitability of (CH₃)₃SiNHTiCl₃ as a binder and as an *in situ* source of TiN to prepare Si₃N₄—TiN and Ti—TiN bodies.

II. Experimental Procedure

Standard inert atmosphere techniques were used in the synthesis and handling of (CH₃)₃SiNHTiCl₃. Dichloromethane was stored over phosphorus pentoxide and distilled before use. Commercial titanium tetrachloride and hexamethyldisilazane were purified by distillation. Elemental analyses were performed by Galbraith Laboratories (Knoxville, TN).

(1) Preparation of $(CH_3)_3$ SiNHTiCl₃

A 250-mL three-necked flask fitted with a condenser was charged with TiCl₄ (6.9 g, 36.3 mmol) and CH₂Cl₂ (100 mL)

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and cooled to -78° C. To this solution, $[(CH_3)_3Si]_2NH$ (5.87 g, 36.3 mmol) was added slowly by syringe with stirring. After the addition was completed, the reaction mixture was warmed slowly to room temperature. An orange precipitate formed (1.0 g), which was filtered. Its analysis (C, 9.32; H, 3.35; N, 5.15; Ti, 22.25; in one example) was not reproducible from reaction to reaction, precluding identification.

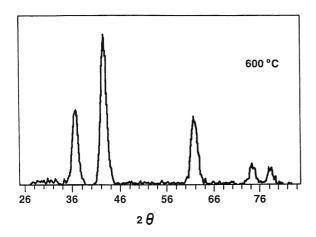
The filtrate was concentrated and cooled to -20° C, yielding 5.16 g (58%) of red-orange crystals. Anal. Calcd for C_3 Cl $_3$ H $_{10}$ NSiTi: C, 14.8; H, 4.16; N, 5.8; Ti, 19.7. Found: C, 15.1; H, 4.2; N, 6.7; Ti, 19.1. IR † (KBr pellet, cm $^{-1}$): 3196 (m, b, ν (NH)), 2975 (ms, ν_{as} (CH) of Me(Si)(N)), 2900 (w, ν_s (CH) of Me(Si)), 1406 (m, δ_{as} (Me(Si))), 1252 (s, δ_s (C–Si) of Me(Si)), 848 (vs, ρ (C–Si) of Me(Si)), 805 (vs, ν (Si–N–Ti)), 763 (s, ρ (Me(Si))), 667 (ν_{as} (SiC $_3$)), 462 (w, ν (Ti–Cl)). ¹H NMR † (CDCl $_3$): δ 0.42. ¹³C NMR: δ (1.98). The compound turned dark at 110°C without melting in a sealed capillary and did not melt even on being heated to 250°C.

(2) Pyrolysis of (CH₃)₃SiNHTiCl₃

The sample (2.0 g) was placed in a quartz tube connected to a system to maintain a dynamic nitrogen atmosphere. The temperature of the furnace was raised at a rate of 5°C/min to 800°C and maintained at that temperature for 5 h. A black residue (0.68 g) was obtained whose X-ray powder diffraction§ pattern matched that of titanium nitride. The elemental analysis for impurity elements: Si, 1.12; Cl, 3.86; C, 0.33.

In another experiment, pyrolysis of a 2.0-g sample of $(CH_3)_3SiNHTiCl_3$ was carried out in a dynamic ammonia atmosphere, heating to 600°C at 5°C/min and holding at 600°C for 4 h. A golden-brown material (0.42 g) was obtained which

[§]PAD V XRD, Scintag, Santa Clara, CA.



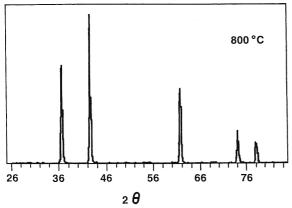


Fig. 1. X-ray powder diffraction patterns of products of pyrolysis (in an NH_3 atmosphere) of [(trimethylsilyl)amino]titanium trichloride.

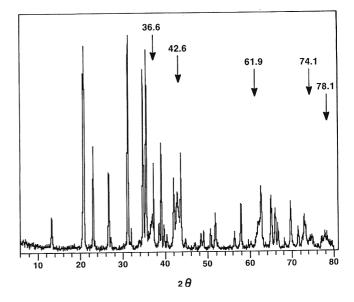


Fig. 2. X-ray powder diffraction pattern of Si_3N_4 -TiN composite powder.

showed broad peaks in its X-ray powder diffraction pattern. Further firing at 800°C for 4 h improved crystallinity and, at 1000°C for 4 h, reduced the carbon content (0.12% as determined by elemental analysis).

(3) Preparation of Silicon Nitride–Titanium Nitride Composites

Dichloromethane was condensed into a mixture of Si_3N_4 powder (2.0 g, particle size less than 1.0 μ m, CERAC) and (CH₃)₃SiNHTiCl₃ (1.57 g). The mixture, a slurry of Si_3N_4 in a solution of (CH₃)₃SiNHTiCl₃, was warmed to room temperature with stirring and the solvent was removed under vacuum with vigorous stirring. The residue was pyrolyzed to 800°C at 5°C/min in an ammonia atmosphere with a 4 h hold at 800°C. The yield was 2.35 g.

In a second experiment, a flask was charged with Si_3N_4 powder (CERAC) (10 g), $(CH_3)_3SiNHTiCl_3$ (3.91 g), and dichloromethane (\sim 40 mL). The solvent was removed with vigorous stirring under vacuum to obtain a free-flowing powder. A portion of this powder was pressed into a green body of size $3.51 \text{ cm} \times 1.2 \text{ cm} \times 0.5 \text{ cm}$ following the procedure described elsewhere. The green body was placed in a furnace and the temperature was raised to $200^{\circ}C$ in argon (hold 2 h), $600^{\circ}C$ in ammonia (hold 2 h), and $1500^{\circ}C$ in argon (hold 2 h). The X-ray powder diffraction pattern showed lines due to β -Si₃N₄, α -Si₃N₄, Si, and TiN. The bulk density of the composite was 1.71 g/cm^3 . The silicon in the composite body originated from the decomposition of silicon nitride (a sample of CERAC Si₃N₄ showed lines due to β -Si₃N₄, α -Si₃N₄, and Si after heating at $1500^{\circ}C$ in argon).

(4) Preparation of Titanium-Titanium Nitride Composites

Titanium powder (8.0 g) was added to a solution of $(CH_3)_3SiNHTiCl_3$ (2.0 g) in 50 mL of dichloromethane and the solvent was removed under vacuum with vigorous stirring. A portion of the resulting powder was heated in argon at $200^{\circ}C$ followed by heating in ammonia at $800^{\circ}C$. The X-ray powder diffraction pattern of the powder showed peaks for titanium and titanium nitride.

The powder also was used to fabricate a green body as described above which was heated at 200°C in argon (hold 2 h), followed by heating at 5°C/min in ammonia at 600°C (hold 2 h) and argon at 1000°C (hold 2 h). The X-ray powder diffraction pattern of the resulting body showed peaks due to Ti and $\rm Ti_2N$. The bulk density of the composite was 2.2 g/cm³.

[†]Galaxy Series FTIR 5000 Spectrometer, Mattson Instruments, Inc., Madison, WI. [‡]WM-360 NMR Spectrometer, Bruker.

III. Results and Discussion

The reactions of TiCl₄ with [(CH₃)₃Si]₂NH were investigated by Andrianov *et al.*²⁰ and Bürger and Wannagat²¹ under different reaction conditions. Andrianov *et al.* proposed formation of "NHTiCl₂" in the absence of solvents while Bürger and Wannagat isolated [(CH₃)₃Si]₂NH·2TiCl₄ and (CH₃)₃SiNHTiCl₃ by varying the reaction conditions and characterized them by elemental analysis.

We have reinvestigated this chemistry and found that "NHTiCl₂" is not formed under the conditions described by Andrianov *et al.*²⁰ We also found that Me₃SiNHTiCl₃ can be prepared in high yield by the addition of [(CH₃)₃Si]₂NH to a dichloromethane solution of TiCl₄ at -78° C. Red-orange crystals of Me₃SiNHTiCl₃ were isolated in 58% yield upon appropriate workup.

$$TiCl_4 + [(CH_3)Si]_2NH \rightarrow [(CH_3)_3SiNHTiCl_3] + Me_3SiCl$$

The infrared spectrum of the product showed $\nu(\text{Si-N-Ti})^{21}$ at 825 cm⁻¹ in addition to expected absorptions for $(\text{CH}_3)_3\text{Si}^{22}$ and TiCl²³ groups. The presence of $\nu(\text{Ti-Cl})$ (terminal) at 462 cm⁻¹ suggests a tetrahedral environment for titanium which is possible only if $(\text{CH}_3)_3\text{SiNHTiCl}_3$ is monomeric. $(\text{CH}_3)_3\text{SiNHTiCl}_3$ is stable over several months in an inert atmosphere and is soluble in aprotic organic solvents.

Thermogravimetric analysis (in argon at 20°C/min) of $(\text{CH}_3)_3\text{SiNHTiCl}_3$ showed a weight loss of 44% in the $120-200^{\circ}\text{C}$ range. Further heating resulted in a gradual weight loss of 11% in the $220-550^{\circ}\text{C}$ range and of 7% in the $550-600^{\circ}\text{C}$ region. The following course can be proposed for the decomposition of $(\text{CH}_3)_3\text{SiNHTiCl}_3$ based on the TGA results:

$$(CH_3)_3SiNHTiCl_3 \overset{-(CH_3)_3SiCl}{\longrightarrow} NHTiCl_2 \overset{-HCl}{\longrightarrow} NTiCl \overset{-Cl}{\longrightarrow} TiN$$

The first step suggested in the decomposition involves a weight loss of 45%, which is in good agreement with the weight loss observed in the 120–200°C range. The next two steps require a total weight loss of 29.5%. However, the observed weight loss is only 18%, which suggests that the pyrolysis of (CH₃)₃SiNHTiCl₃ in argon furnishes contaminated TiN. Silicon and chlorine contamination has been previously observed in the pyrolysis of Me₃SiAlCl₂.²⁴

The pyrolysis of (CH₃)₃SiNHTiCl₃ in nitrogen to 800°C left a black powder. The X-ray powder diffraction (XRD) pattern of this black powder showed only crystalline titanium nitride (JCPD No. 38,1420) to be present.²⁵ Thus, any contaminants probably are amorphous. Elemental analysis showed the presence of 1.12% Si, 3.86% Cl, and 0.33% carbon in the sample. This supports our inference from TGA data.

The pyrolysis of $(CH_3)_3SiNHTiCl_3$ in an ammonia atmosphere to $600^{\circ}C$ furnished a golden material which could be ground to a dark-olive-brown powder. The peaks due to TiN in the XRD pattern of the powder were somewhat broad, suggesting a small particle size (Fig. 1). After the samples had been heated at $800^{\circ}C$, the resulting powder showed sharp peaks in its XRD pattern (Fig. 1). Transmission electron micrographs (TEM) showed the particle size to be in the 40-200 nm range. Energy dispersive spectra (EDS) of several particles showed $K\alpha$ peaks for titanium and nitrogen but no peaks for silicon or chlorine. Only a small amount of carbon (0.12%) was found by elemental analysis. These data show that titanium nitride is fairly pure. The titanium nitride yield was 80% based on titanium in $(CH_3)_3SiNHTiCl_3$.

In principle, (CH₃)₃SiNHTiCl₃ can be deposited on the surface of any substrate from its solution and fired to prepare TiN on the substrate. To demonstrate this, we deposited (CH₂)₃SiNHTiCl₃ on commercial Si₃N₄ and titanium powders and fired the samples in an ammonia atmosphere to prepare Si₃N₄-TiN and Ti-TiN composites. The X-ray powder diffraction pattern of the Si₃N₄-TiN powder showed diffraction peaks for α - and β -Si₃N₄ and TiN (Fig. 2) and that of the Ti-TiN sample showed peaks due to titanium and titanium nitride. The particle size of the TiN component in Si₃N₄-TiN is 300-500 Å as estimated from the Scherrer equation. This procedure is expected to concentrate the TiN component on the surface of the silicon nitride particles. To find support for this, the Si₃N₄-TiN samples were examined by high-resolution electron microscopy (HREM).^{††} The atomic structure of particles of thickness less than 10 nm can be resolved directly without the need to thin the sample. Figure 3(a) shows a single Si₃N₄ particle decorated with numerous smaller structures of size range 5-20 nm. The observed size range is consistent with the X-ray diffraction results above, which display peak broadening. The small particles were found to occur on the SiN surface as per Fig. 3(b). The inset to Fig. 3(b) represents the Fourier

^{††4000}EX HREM, JEOL, Peabody, MA.

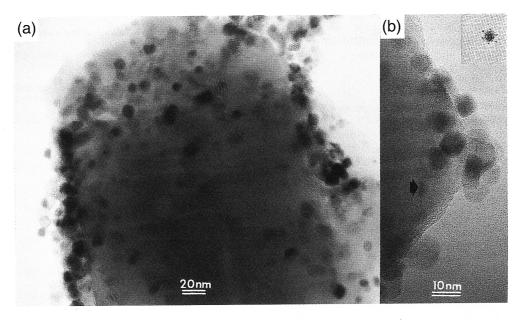


Fig. 3. High-resolution electron micrograph of TiN-Si₃N₄ powders.

TA7 Thermogravimetric Analyzer, Perkin-Elmer, Eden Prairie, MN.

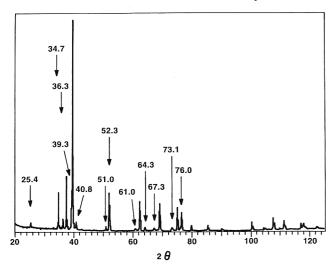


Fig. 4. X-ray powder diffraction pattern of Ti–Ti₂N composite body.

power spectrum of one such particle in a zone axis orientation (indicated by an arrow). The aspect ratio of this pattern closely matches that of a face-centered cubic structure, looking along a (011) type zone axis. Measurements of the reciprocal lattice vectors of this pattern were calibrated with reference to similar measurements of the [011] zone axis power spectrum from a silicon standard. The results indicate interplanar spacings of 0.236 and 0.202 nm, which compare favorably with the {111} and {002} spacings of TiN (0.245 and 0.212 nm, respectively). Since atomic structure images arise from areas within 5–10 nm of the free surface, these particles must reside in this region. These results clearly show that the titanium nitride component of the composites is concentrated near the surface.

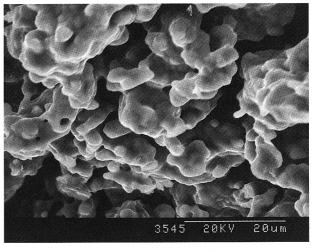
The fabrication of Si_3N_4 –TiN and Ti–TiN bodies was carried out by the procedure described by Czubarow and Seyferth. The X-ray powder diffraction of the Si_3N_4 –TiN composite body was similar to the one obtained for the powder described above except that the diffraction peaks due to TiN are sharp, suggesting sintering of the fine particles. Additional peaks due to elemental silicon also are present.

The X-ray powder diffraction pattern of the Ti–TiN body showed diffraction peaks due to elemental titanium and nitrogen-deficient titanium nitride, Ti₂N (Fig. 4). The formation of Ti₂N is due to reaction of TiN with Ti metal. The SEM of the body showed high porosity (Fig. 5). The bulk densities of Si₃N₄–TiN and Ti–TiN bodies prepared by using (CH₃)₃ SiNHTiCl₃ as binder were 1.71 and 2.2 g/cm², respectively. Further experiments are in progress using standard hot-pressing methods to improve the densities of composites.

IV. Conclusions

Reaction of titanium tetrachloride with hexamethyldisilazane in dichloromethane furnished (CH₃)₃SiNHTiCl₃ which is soluble in common organic solvents. This precursor formed titanium nitride on pyrolysis in an ammonia atmosphere at 600° C. Si₃N₄–TiN and Ti–TiN composites with TiN content concentrated on the surface of the substrate particles were prepared by depositing (CH₃)₃SiNHTiCl₃ on Si₃N₄ or Ti particles followed by pyrolysis. Thus, this method offers a low-temperature route to titanium nitride and a convenient preparation of composites with the TiN content concentrated on the surface. (CH₃)₃-SiNHTiCl₃ also can be used as a binder in the fabrication of ceramic or metal-matrix composite bodies.

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(a)

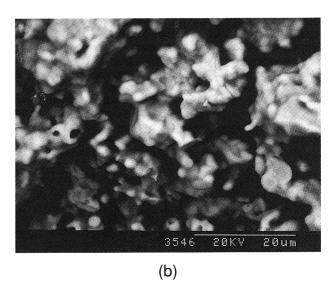


Fig. 5. Scanning electron micrographs of Ti-Ti₂N body.

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